

L Number	Hits	Search Text	DB	Time stamp
1	2	("20010054724").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:03
2	247	(Junction near field near effect near transistor JFET) with (metal near oxide near silicon MOS MOSFET) with (bipolar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:07
3	619	(438/144,60,75,for.213).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:06
4	0	("002and3").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:07
5	0	((Junction near field near effect near transistor JFET) with (metal near oxide near silicon MOS MOSFET) with (bipolar)) and ((438/144,60,75,for.213).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:07
6	96	((Junction near field near effect near transistor JFET) with (metal near oxide near silicon MOS MOSFET) with (bipolar)) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:07
7	17	(photo adj diode photodiode) and ((Junction near field near effect near transistor JFET) with (metal near oxide near silicon MOS MOSFET) with (bipolar))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 09:08